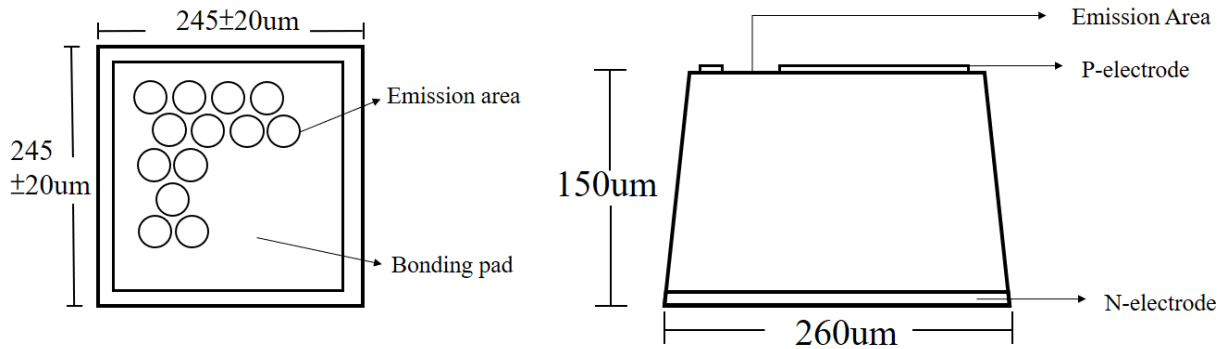


■ **Features & Applications :**

- 940 nm Wavelength
- Low Dependence of Electrical and Optical Characteristics over Temperature
- Optical Sensing

■ **Outline Dimensions : (Unit: μm)**



■ **Physical Structure :**

Chip dimension	Chip size	260 μm x 260 μm
	Thickness	150 \pm 25 μm
Electrode	N(cathode)	Gold
	P (anode)	Gold

■ **Electro-Optical Characteristics :**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Output Power	P_o	IF = 60 mA	40	45	50	mW
Forward Voltage	VF	IF = 60 mA	1.8	2.1	2.3	V
Threshold Current	I _{th}	-	3	6.5	9	mA
Wavelength	λ_p	IF = 60 mA	935	940	945	nm
Beam Divergence (1/e ²)	θ	IF = 60 mA	-	22	-	degree